

ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18

Stylesheet Version v18.0

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| Title of Invention | STRUCTURE AND METHOD OF MAKING HETEROJUNCTION BIPOLAR TRANSISTOR HAVING SELF-ALIGNED SILICON-GERMANIUM RAISED EXTRINSIC BASE |
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Application Number :

Confirmation Number:

First Named Applicant: Kevin Chan

Attorney Docket Number: FIS920030310US1

Art Unit:

Examiner:

Search string: (5128271 or 5494836 or 5506427 or 5962880 or 6346453).pn

US Patent Documents

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

| init | Cite.No. | Patent No. | Date | Patentee | Kind | Class | Subclass |
|------|----------|------------|------------|-----------------|------|-------|----------|
| | 1 | 5128271 | 1992-07-07 | Bronner, et al. | | | |
| | 2 | 5494836 | 1996-02-27 | Imai | | | |
| | 3 | 5506427 | 1996-04-09 | Imai | | | |
| | 4 | 5962880 | 1999-10-05 | Oda, et al. | | | |
| | 5 | 6346453 | 2002-02-12 | Kovacic, et al. | | | |

Signature

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| Examiner Name | Date |
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